

MANUFACTURE OF SEMICONDUCTOR ELEMENT

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Patent Number: JP1143233

Publication date: 1989-06-05

Inventor(s): IWATA NAOTAKA

Applicant(s): NEC CORP

Requested Patent: JP1143233

Application Number: JP19870300950 19871127

Priority Number(s):

IPC Classification: H01L21/76; C30B25/02; H01L21/205; H01L29/04; H01L29/80

EC Classification:

EC Classification:

Equivalents:

Abstract

PURPOSE: To achieve electrical isolation between elements easily by a method wherein plateau-shape structures which have required faces are exposed on the surface of a group IV crystal substrate and then a III-V compound semiconductor layer is formed by an atomic layer epitaxial growth method.

CONSTITUTION: GaCl and AsH₃ are employed as group III raw gas and group V raw gas respectively and atomic layer epitaxial growth is repeated 2000 times on a wafer at 450 deg.C. The film thickness of a GaAs growth layer 19 obtained by slant polishing is, for instance, 7000Angstrom on a face (211) and 4000Angstrom on a face (110). AuGe ohmic contacts 20 are formed on four corners of the upper surface of each plateau-shape structure of the wafer. Electric conduction is recognized between the ohmic contacts formed on the same face (211) and, by a Hall measurement, the conductivity type is n-type and the carrier concentration is 1X10<16>cm<-3>. On the other hand, the electric conduction is not recognized between adjoining plateau-type growth layers so that the electrical isolation between elements can be achieved completely. Thus, the electrical isolation between the elements can be achieved easily without making a process complicated.